

Daniele Baretin

List of Publications by Year in descending order

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160
citing authors

#	ARTICLE	IF	CITATIONS
1	Nanophotonics for Perovskite Solar Cells. <i>Advanced Photonics Research</i> , 2022, 3, .	3.6	15
2	Optimization of InGaN quantum-dot based light-emitting diodes by means of cellular automata algorithms. <i>Optical and Quantum Electronics</i> , 2022, 54, .	3.3	1
3	Charge Transport Mechanisms of Black Diamond at Cryogenic Temperatures. <i>Nanomaterials</i> , 2022, 12, 2253.	4.1	2
4	Piezo-electric fields and state-filling photo-luminescence in natural InP/GaNP2 Wigner molecule structures. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	5
5	Fabry-Perot Pressure Sensors Based on Polycrystalline Diamond Membranes. <i>Materials</i> , 2021, 14, 1780.	2.9	8
6	Piezoelectric tunability and topological insulator transition in a GaN/InN/GaN quantum-well device. <i>JPhys Materials</i> , 2021, 4, 034008.	4.2	1
7	SiC and Diamond Membrane Based Pressure Sensors for Harsh Environments. , 2021, , .		0
8	Electromechanical field effects in InAs/GaAs quantum dots based on continuum $\hat{k} \cdot \hat{A} \cdot \hat{p}$ and atomistic tight-binding methods. <i>Computational Materials Science</i> , 2021, 197, 110678.	3.0	11
9	Giant Enhancement of Radiative Recombination in Perovskite Light-Emitting Diodes with Plasmonic Core-Shell Nanoparticles. <i>Nanomaterials</i> , 2021, 11, 45.	4.1	12
10	Engineering the Charge Transport Properties of Resonant Silicon Nanoparticles in Perovskite Solar Cells. <i>Energy Technology</i> , 2020, 8, 1900877.	3.8	12
11	Carrier transport and emission efficiency in InGaN quantum-dot based light-emitting diodes. <i>Nanotechnology</i> , 2017, 28, 275201.	2.6	13
12	Excitonic lasing of strain-free InP(As) quantum dots in AlInAs microdisk. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	3
13	Influence of electromechanical coupling on optical properties of InGaN quantum-dot based light-emitting diodes. <i>Nanotechnology</i> , 2017, 28, 015701.	2.6	14
14	A valence force field-Monte Carlo algorithm for quantum dot growth modeling. , 2017, , .		0
15	Realistic model of LED structure with InGaN quantum-dots active region. , 2015, , .		0
16	Inter-dot strain field effect on the optoelectronic properties of realistic InP lateral quantum-dot molecules. <i>Journal of Applied Physics</i> , 2015, 117, 094306.	2.5	12
17	Realistic models of quantum-dot heterostructures. , 2014, , .		0
18	Model of a realistic InP surface quantum dot extrapolated from atomic force microscopy results. <i>Nanotechnology</i> , 2014, 25, 195201.	2.6	25

#	ARTICLE	IF	CITATIONS
19	Optimization by record dynamics. Computer Physics Communications, 2014, 185, 730-735.	7.5	1
20	Modelling of GaAs quantum dot embedded in a polymorph AlGaAs nano wire. , 2013, , .		0
21	Model of a GaAs Quantum Dot Embedded in a Polymorph AlGaAs Nanowire. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1-9.	2.9	16
22	Effect of dielectric Bragg grating nanostructuring on dye sensitized solar cells. Optics Express, 2012, 20, A888.	3.4	21
23	Effect of dielectric Bragg grating nanostructuring on dye sensitized solar cells. Optics Express, 2012, 20, A888-97.	3.4	4
24	Strain and piezoelectric effects in quantum-dot structures. , 2011, , .		1
25	Entropic algorithms and the lid method as exploration tools for complex landscapes. Physical Review E, 2011, 84, 036706.	2.1	3
26	Comparison of continuum and atomistic methods for the analysis of InAs/GaAs quantum dots. , 2011, , .		2
27	Band-mixing and strain effects in InAs/GaAs quantum rings. Superlattices and Microstructures, 2010, 47, 103-107.	3.1	2
28	Comparison of wurtzite atomistic and piezoelectric continuum strain models: Implications for the electronic band structure. Superlattices and Microstructures, 2010, 47, 134-138.	3.1	14
29	Piezoelectric models for semiconductor quantum dots. Microelectronics Journal, 2008, 39, 1226-1228.	2.0	10